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Product Portfolio Photoresists

We deliver our products within 1 week ex work, in-stock stock items are delivered immediately or on the desired date. Resists are available in package sizes of ¼ ℓ, 0,5 ℓ, 1 ℓ, 2,5 ℓ, 6 x 1 ℓ, 4 x 2,5 ℓ and corresponding process chemicals in package sizes of 1 ℓ, 2,5 ℓ, 5 ℓ, 4 x 2,5 ℓ, 4 x 5 ℓ. Test samples/smallest quantities of 30 ml and 100 ml are possible.Please request our price lists.

Resist system	Product	Do/ µm 4000 rpm	Type	Characteristic Properties	Applica-tion	Resolution [µm]	Con-trast	Expo-sure	Thinner	Deve-loper	Remo-ver
AR-P 1200	1210,1220, 1230	[0.5 - 10]	positive resist	spray resist, var. applications	MEMS	1	3	i-line, g-line, BB-UV	-	300-44	600-71 300-73
AR-P 3100	3110, 3120, 3170	1,0 ; 0,6 ; 0,1		high resolution, adhesion-enhanced	masks, lattices	0.5 ; 0.4 ; 0.4	3.0		300-12	300-35 300-26	300-76 300-73
AR-P 3200	3210, 3220, 3250	10 ; 10 ; 5		thick resist with high dimen. accuracy up to 100 µm	electro-plating, MST	4 ; 3 ; 1.2	2.0 ; 2.0 ; 2.5		300-12	300-26	600-71 300-76
AR-P 3500	3510, 3540	2.0 ; 1.4		wide process range, high resolution	ICs	0.8 ; 0.7	4.0 ; 4.5		300-12	300-35 300-26	600-71 300-73
AR-P 3500 T	3510 T, 3540 T	2.0 ; 1.4		wide process range, high res., developable in 0.26 n TMAH	ICs	0.6 ; 0.5	4.5 ; 5.0		300-12	300-44 300-26	300-76 600-71
AR-P 3700, 3800	3740, 3840	1.4 ; 1.4		highest resolution, sub-µm, high cont-rast, 3840 dyed	VLSIC	0.4 ; 0.4	6.0 ; 6.0		300-12	300-47 300-26	600-71 300-76
AR-P 5300	5320, 5340	5.0 ; 1.0		undercut structures (single layer lift-off)	evapor-ation structures	2 ; 0.5	4 ; 5		300-12	300-26	600-76 300-73
AR-U 4000	4030, 4040 4060	1.8 ; 1.6 ; 0.6	special application	optinally pos. or neg., lift off	ICs	0.8 ; 0.7; 0.5	3 ; 3 ; 3.5		300-12	300-35 300-26	600-72 300-76
AR-PC 500	503 dyed 504, 5040	1.2 ; 2.2		protective coating, 40% KOH etch-stable	protecti-ve film	-	-	-	600-01	-	600-71 300-76
AR-BR 5400	5460, 5480	1.0 ; 0.5		bottom resist for 2L lift-off	lift-off (pos./neg.)	3 ; 1.5	lift-off	-	-	-	300-73 300-76
AR-P 5900	5910	5.0		complicated patten. up to 5 % HF / BOE	MEMS	2	2.0	i-line, g-line, BB-UV	300-12	300-26	300-76 300-73
AR-N 2200	2210, 2220, 2230	[0.5 - 10]	negative resist	spray resist, var. applications	MEMS	1	3		-	300-44	600-71 300-73
AR-N 4200	4240	1.4		highly sensitive, high resolution	ICs	0.6	2.8	deep UV, i-line	300-12	300-26 300-47	600-71 300-76
AR-N 4300	4340	1.4		highest sensitivity, high resolution, CAR	ICs	0.5	5	i-line, g-line	300-12	300-26 300-475	600-76 300-72
AR-N 4400	4400-50, -25, -10, -05	1000 rpm: 50 ; 25 ; 10 ; 5		thick films up to 100, 50, 20, 10 µm, easy removal	electro-plating, MST, LIGA	5.0 ; 3.5 ; 2.0 ; 1.0	6 ; 5 ; 4 ; 4	X-ray, e-beam, i-line	300-12	300-44 bis -475	600-71 600-70
AR-N 4450	4450-10	1000 rpm: 10		thick films up to 20 µm, lift-off		2.0 3.5	10 lift-off		300-12	300-47	600-71 600-70

All resist systems show optimal adhesion features with adhesion promoter AR 300-80 which is applied prior to resist deposition.

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ALLRESIST

Product Portfolio E-Beam Resists

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Resist system	Product	Do/ µm 4000 rpm	Type	Characteristic Properties	Application	Resolution [µm] *	Contrast	Exposure	Thinner	Developer	Remover
AR-P 617	copolymer PMMA/MA 33%	0.09-1.75 methoxy propanole	positive	highest resolution, 2x more sensitiver than PMMA, lift off	ICs, masks	10 / 100	6.0	e-beam, deep UV	600-07	600-50 600-55	600-71 300-76
AR-P 631-671	PMMA 50K, 200K, 600K, 950K	0.02-1.70 chlorobenzene	positive	highest resolution, process stable, universally, simple processing	ICs, masks	6 / 100	7.0	e-beam, deep UV	600-01	600-55 600-56	600-71 300-76
AR-P 632-672	PMMA 50K, 200K, 600K, 950K	0.01-1.87 anisole	positive	highest resolution, process stable, universally, simple processing	ICs, masks	6 / 100	7.0	e-beam, deep UV	600-02	600-55 600-56	600-71 300-76
AR-P 639-679	PMMA 50K, 200K, 600K, 950K	0.02-0.74 ethyl lactate	positive	highest resolution, process stable, universally, simple processing	ICs, masks	6 / 100	7.0	e-beam, deep UV	600-09	300-55 300-56	600-71 300-76
AR-P 6200 new CSAR 62	6200.04, .09, 6200.13 styrene acrylate	0.08 ; 0.4 ; 0.2	positive	highest resolution, high sensitivity, plasma etching-resistant	ICs, sensors, masks	6	15	e-beam, deep UV	600-02	600-546 600-548 600-549	600-71 300-76
AR-P 6500	6510.17, .18, 6510.19 PMMA	350 rpm: 45. 80. 150	positive	thick PMMA films up to 250 µm for MST, synchrotron	micro components	1 µm (x-ray)	10 (x-ray)	x-ray, e-beam	300-12	600-51 600-56	600-71 300-76
AR-P 7400	7400.23 novolac	0.6	positive	mix&match, high resolution, plasma etching-resistant, also neg.	ICs, masks	40 / 150	4.0	e-beam, deep UV, g-line, i-line	300-12	300-47 300-26	300-76 600-71
AR-N 7500	7500.08, 7500.18 novolac	0.1 ; 0.4	negative	mix&match, high resolution, plasma etching-resistant, pos./neg.	ICs, masks	40 / 100	5.0	e-beam, deep UV, g-line, i-line	300-12	300-47	600-71 300-73
AR-N 7520 new	7520.07, .11, 7520.17 novolac	0.1 ; 0.2; 0.4	negative	mix&match, highest resolution, plasma etching resistent	ICs, masks	30	8.0	e-beam, deep UV, i-line,	300-12	300-46 300-47	600-71 300-73
AR-N 7700	7700.08, 7700.18 novolac	0.1 ; 0.4	negative	CAR, high resolution, high sensitivity, steep gradation	ICs, masks	80 / 100	5.0	e-beam, deep UV	300-12	300-46 300-47	300-76 300-73
AR-N 7720	7720.13, 7720.30 novolac	0.25 ; 1.4	negative	CAR, high resolution, flat gradation for 3-dimens. struct.	diffract. optics	80 / 200	< 1.0	e-beam, deep UV	300-12	300-46 300-47	300-76 300-72
AR-PC 5000	polyaniline 5090.02 5091.02	0,04 ; 0,03		conductive protective Coating for the dissipation of charges PMMA e-beam resists (PMMA, CSAR 62, HSQ) Novolac e-beam resists (e.g. AR-N 7500, 7700)					-	-	DI water

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Resists AR-P 617, 631-679, 6200 require brief stopping in stopper AR 600-60 after development.

As of January 2016

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Product Portfolio Experimental Samples

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Special product	Do/ µm 4000 rpm	Type	Characteristic properties / Application	Resolution [µm] *	Contrast	Exposure	Thinner	Developer	Remover
Market-ready experimental samples									
X AR-P 3220/7	6.0	positive	temperature-/ plasma etching stable thick resist	2	2	i-line. g-line, BB-UV	300-12	300-26	300-76 300-72
X AR-P 5900/4	1.4		positive photoresist, alkali-stable up to pH 13	1	2	i-line, g-line	300-12	300-26	600-70
X AR-N 7700/30	0.4	neg.	highly sensitive, highest-resolution CA negative e-beam resist	0.2	5	e-beam, deep UV	300-12	300-475	600-70 300-76
Special designs / Experimental samples									
SX AR-P 3500/6	2.0	positive	positive photoresist for holography (488 nm)	1	3	i-line. g-line, BB-UV	300-12	300-47	600-70 300-76
SX AR-P 3500/8	1,4		temeratur stable positive photoresist up to 300 °C	1	3	i-line. g-line, BB-UV	300-12	300-47	600-70 300-76
SX AR-P 3740/4	1.4		positive photoresist, highly process-stable, high contrast	0.6	5	i-line. g-line, BB-UV	300-12	300-475	600-70 300-76
SX AR-N 4340/7	1.4	neg.	temperature stable negative resist up to 270 °C (1-/2L-system)	0.5	5	i-line, g-line	300-12	300-47	300-76 600-71
SX AR-PC 5000/22.2	0.02	-	protective coating for spray application, smooth surface	-	-	-	600-09	-	600-70 300-76
SX AR-PC 5000/40	5.0	-	protective coating 40% KOH- and 50% HF-resistant	1 L: - 2 L: 10	1 L: - 2 L: 1	1 L: - 2 L: i-line	300-74/1	300-26	300-74/1
SX AR-PC 5000/80.2	0.4	-	polyimide photoresist, protective coating for 2 L-patterning	1 L: - 2 L: 2	1 L: - 2 L: 1	1 L: - 2 L: i-line	300-12/3	-	600-70 300-76
SX AR-P 5000/82.7	0.8	-	polyimide photoresist, structurable and temperature-stable	1.5	2	i-line	300-12/3	300-26 300-47	300-76 300-72
SX AR-N 7530 new	0,1	negative	white light e-beam resist like AR-N 7520	0.03	8	e-beam, deep UV	300-12	300-47	600-71
SX AR-N 7730 new			white light e-beam resist like AR-N 7700	0.08	< 1.0				300-76

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